

G-1/188/22

Roll No.

I Semester Examination, January 2022

M.Sc.

PHYSICS

Paper IV

(Electronic Devices)

Time : 3 Hours]

[Max. Marks : 80

Note : All questions are compulsory. Question Paper comprises of 3 Sections. Section A is objective type/multiple choice questions with no internal choice. Section B is short answer type with internal choice. Section C is long answer type with internal choice.

SECTION A

1×8=8

(Objective Type/Multiple Choice Questions)

Choose the correct answer :

1. A change of 200 mv in base emitter voltage causes a change of 100 μ A in the base current. The input resistance of the transistor is :
- (a) 0.2 k Ω (b) 2 k Ω
(c) 2 Ω (d) 20 k Ω

P.T.O.

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2. In N channel JFET, the current is due to the flow of :
(a) holes alone
(b) holes and electron both
(c) electrons alone
(d) either holes or electron.
3. Digital camera works on a principle of :
(a) IMPATT diode (b) Backward diode
(c) Gun diode (d) CCD
4. In P-type semiconductor MIS diode which of the following occurs when $V < 0$:
(a) Depletion (b) Inversion
(c) Accumulation (d) All of these
5. Piezoelectricity is shown by substance which are :
(a) Polar (b) Non-Polar
(c) Symmetric (d) Asymmetric
6. The optical properties of liquid crystals depends on the direction of :
(a) Air (b) Solid
(c) Light (d) Water

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7. A carrier wave of 1 MHz is modulated with audio frequency varying between 20 Hz to 20 kHz. The frequency possible in lower side band is :

- (a) 900 kHz (b) 930 kHz
(c) 960 kHz (d) 990 kHz

8. In the single side band transmission :

- (a) The channel width decreases
(b) The power consumption increases
(c) The distortion increases
(d) The secrecy of information is lost

SECTION B

6×4=24

(Short Answer Type Questions)

Note : Answer the following questions.

1. Explain current gain in different modes and determine relation between them.

Or

Explain working principle of e-MOSFET.

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P.T.O.

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2. Explain tunnel diode with the help of energy band diagram.

Or

Explain transferred electron mechanism.

3. Explain electro-optic device.

Or

Explain electrostrictive effects.

4. What is Amplitude Modulation ? Explain percentage of modulation.

Or

Explain working of linear detector.

SECTION C

12×4=48

(Long Answer Type Questions)

Note : Answer the following questions.

1. Describe construction working principle and characteristic curve of UJT.

Or

Explain the construction and working of a P-channel DE-MOSFET and describe its characteristics curves.

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- 2.** What is CCD ? Explain construction and working of CCD.

Or

Derive an expression for electric field for an MIS diode and explain variation of space-charge density as a function of surface potential.

- 3.** Explain the following :

- (a) Piezoelectric resonators
- (b) Liquid crystal.

Or

- (a) Acousto-optic material as sensor
- (b) Magneto strictive effect.

- 4.** How is a transistors used as an amplitude modulator ? Draw the circuit diagram and explain its working.

Or

Obtain an expression of output voltage for square law detector.

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